

IN THE CLAIMS

Please amend the claims as follows:

Claims 1-10 (Canceled).

Claim 11 (Currently Amended): A method of manufacturing a semiconductor device comprising a capacitor which has a first electrode film, a second electrode film being provided above the first electrode film, and a capacitor insulating film provided between the first and second electrode films, said method comprising:

forming a protective insulating film between the capacitor insulating film and the second electrode film or on the second electrode film;

forming [[a]] an insulating film on the capacitor;

forming a first trench configured to expose a part of the first electrode film, and a second trench configured to expose a part of the second electrode film;

performing heat treatment which uses a hydrogen-containing gas; and

forming in the first trench a first connection part electrically connected to the first electrode, and forming in the second trench a second connection part electrically connected to the second electrode film.

Claim 12 (Original): A method according to claim 11, further comprising:

forming a first wiring trench and a second wiring trench before the heat treatment is performed, said first and second wiring trenches continuing with the first and second trenches, respectively; and

forming a first wiring and a second wiring in the first and second wiring trenches, respectively, at the same time the first and second connection parts are formed.

Claim 13 (Original): A method according to claim 11, wherein, the protective insulating film has relative dielectric constant ϵ of at least 10.

Claim 14 (Original): A method according to claim 11, wherein $10 \leq \epsilon \leq 30$, where ϵ is relative dielectric constant of the protective insulating film.

Claim 15 (Original): A method according to claim 11, wherein $10 \text{ nm} \leq X \leq 20 \text{ nm}$, where X is a thickness of the protective insulating film.

Claim 16 (Original): A method according to claim 11, wherein the protective insulating film has a thickness X that ranges from 10% to 40% of the thickness of the capacitor insulating film.

Claim 17 (Original): A method according to claim 11, wherein the capacitor insulating film is a tantalum oxide film.

Claim 18 (Original): A method according to claim 11, wherein the protective insulating film is an aluminum oxide film.

Claim 19 (Original): A method according to claim 11, wherein the capacitor is formed on a diffusion-preventing film.

Claim 20 (Original): A semiconductor device according to claim 12, wherein the first wiring and the second wiring are formed of copper.

Claim 21 (Original): A method according to claim 11, wherein the first connection part and the second connection part are formed of copper or tungsten.

Claim 22 (New): A method according to claim 11, wherein the first electrode film and the second electrode film are formed of a titanium nitride film.

Claim 23 (New): A method according to claim 11, wherein the capacitor insulating film has a first side where the first electrode film is present and a second side where the second electrode film is present, and the protective insulating film is formed only on the second side.

Claim 24 (New): A method according to claim 11, wherein the protective insulating film is formed only on the second electrode film located opposite the capacitor insulating film.

Claim 25 (New): A method according to claim 11, wherein the capacitor insulating film is in direct contact with the first electrode film.

Claim 26 (New): A method according to claim 11, wherein the protective insulating film prevents reduction of the capacitor insulating film.